L Number	Hits		DB	Time stamp
1	203		USPAT;	2002/11/27 22:41
İ		deposit\$4 same (CVD with PVD))	US-PGPUB;	ļ
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB USPAT;	2002/11/27 22:31
2	14	(semiconductor and ((tungste or W) same	US-PGPUB;	2002/11/2/ 22:31
		deposit\$4 same (CVD with PVD))) and SOI	EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	1781	(438/106-110).CCLS.	USPĀT	2002/11/27 22:40
4	1	((438/106-110).CCLS.) and (tungste or W)	USPAT;	2002/11/27 22:41
•	_	and LTO	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	1	((438/106-110).CCLS.) and (tungste or W)	USPĀT;	2002/11/27 22:45
		and (low with temperature with oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_		semiconductor and SOI and (substrate with	IBM_TDB USPAT;	2002/11/27 22:44
6	38	bond\$4) and (tungste or W) and (low with	US-PGPUB;	2002/11/2/ 22:44
		temperature with oxide)	EPO; JPO;	
		temperature with oxide,	DERWENT;	
			IBM TDB	
8	5	((438/106-110).CCLS.) and (tungsten) and	USPĀT;	2002/11/27 22:45
-		(low with temperature with oxide)	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	25	semiconductor and SOI and (substrate with	USPAT;	2002/11/27 22:48
		bond\$4) and (tungsten) and (low with	US-PGPUB;	
1		temperature with oxide)	EPO; JPO;	
			DERWENT; IBM TDB	
9	0	semiconductor and SOI and (substrate with	USPAT;	2002/11/27 22:49
ש	U	bond\$4) and (tungsten) and (low with	US-PGPUB;	2002/11/2/ 22.19
		temperature with oxide) and (oxigen with	EPO; JPO;	,
		migration)	DERWENT;	
	'		IBM TDB	
10	5	semiconductor and (substrate with bond\$4)	USPĀT;	2002/11/27 22:49
		and ((tungsten) same barrier same (low	US-PGPUB;	
		with temperature with oxide))	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	L

US-433331-S or US-6450994-\$ or US-620UB; EPC; JPO; US-6410705-\$ or US-6410436-\$ or US-633202-\$ or US-633202-\$ or US-6333012-\$ or US-6333012-\$ or US-6303102-\$ or US-630302-\$ or US-6103194-\$ or US-6150031-\$ or US-6100359-\$ or US-6103598-\$ or US-6120139-\$ or US-6103598-\$ or US-6103090-\$ or US-6103598-\$ or US-6103090-\$ or US-6103598-\$ or US-6103090-\$ or US-6103598-\$ or US-6103090-\$ or US-610555-\$ or US-6054363-\$ or US-536620-\$ or US-537355-\$) did. or (US-56620-\$ or US-5937312-\$ or US-536620-\$ or US-5336361-\$ or US-5492839-\$ or US-5336361-\$ or US-533934-\$ or US-5346331-\$ or US-53710375-\$ or US-533934-\$ or US-53740375-\$ or US-533934-\$ or US-5346331-\$ or US-533934-\$ or US-5346331-\$ or US-533934-\$ or US-5346331-\$ or US-533934-\$ or US-533935-\$ or US-5346831-\$ or US-533934-\$ or US-533935-\$ or US-534683-\$ or US-530876-\$ or US-5330876-\$ or US-530876-\$ or US-5204607-\$ or US-5204607-\$ or US-5204607-\$ or US-20020094663-\$ or US-20020094693-\$ or US-20020094663-\$ or US-20020094693-\$ or US-20020094663-\$ or US-20020094693-\$ or US-2002009470-\$ or US-2002009470-\$ or US-2002009470-\$ or US-2002009470-\$ or					
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US-6417075-\$ or US-6410436-\$ or US-6330102-\$ or US-6303122-\$ or US-630312-\$ or US-630312-\$ or US-6103139-\$ or US-6106729-\$ or US-6100319-\$ or US-6100319-\$ or US-6103598-\$ or US-6103199-\$ or US-6103598-\$ or US-6103190-\$ or US-6103598-\$ or US-60540363-\$ or US-5966620-\$ or US-5937312-\$ or US-5966620-\$ or US-5937312-\$ or US-5966620-\$ or US-5937312-\$ or US-540611-\$ or US-533631-\$ or US-5492899-\$ or US-5336361-\$ or US-5339241-\$ or US-5339241-\$ or US-5339394-\$ or US-5339581-\$ or US-5349819-\$ or US-5349819-\$ or US-534981-\$ or US-5249748-\$ or US-5249748-\$ or US-5249748-\$ or US-526920-\$ or US-2020008646-\$ or US-20200086469-\$ or US-20200086470-\$ or US-2020086470-\$ or US-2020086470-\$ or US-2020086470-\$ or US-2020086470-\$ or US-2020086470-\$ or US-2020086470-\$					Į.
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US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6150031-\$ or US-616879-\$ or US-6103699-\$ or US-6103699-\$ or US-6103699-\$ or US-6103699-\$ or US-6045626-\$ or US-5985739-\$ or US-596620-\$ or US-5985739-\$ or US-596620-\$ or US-5937312-\$ or US-596620-\$ or US-5937312-\$ or US-5492839-\$ or US-539531-\$ or US-5492839-\$ or US-5336361-\$ or US-5492839-\$ or US-533941-\$ or US-5399231-\$ or US-5399231-\$ or US-5399231-\$ or US-533941-\$ or US-5337451-\$ or US-5337429-\$ or US-5317481-\$ or US-5317481-\$ or US-5317481-\$ or US-531749-\$ or US-531749-\$ or US-5277748-\$ or US-528322-\$ or US-5244817-\$ or US-526322-\$ or US-5244817-\$ or US-526322-\$ or US-5244817-\$ or US-526322-\$ or US-229305-\$ or US-4829018-\$ or US-4829018-\$ or US-4829018-\$ or US-2002009861-\$ or US-20020036463-\$ or US-20020036463-\$ or US-20020036463-\$ or US-2002003729-\$ or US-20020086470-\$ or US-2002008649-\$ or US-20020002237-\$ or US-20020002234-\$ or US-20020002237-\$ or US-2002002237-\$ or US-20020002234-\$ or US-20020002237-\$ or US-20020002234-\$ or US-20020002237-\$ or US-20020002237-\$ or US-20020002237-\$ or US-20010002350-\$ or US-20010002550-\$ or US-20010002550-\$ or US-20010002550-\$ or US-20010002550-\$ or US-20010002550-\$ or US-20010002550-\$ or US-20050005000000000000000000000000000000					
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US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5492859-\$ or US-5459843-\$ or US-5399231-\$ or US-549843-\$ or US-5399231-\$ or US-5395881-\$ or US-5374581-\$ or US-5395881-\$ or US-5374581-\$ or US-5374229-\$ or US-5374681-\$ or US-5374229-\$ or US-5374681-\$ or US-5374229-\$ or US-5324678-\$ or US-5366924-\$ or US-5258322-\$ or US-5244817-\$ or US-5258322-\$ or US-5244817-\$ or US-5258322-\$ or US-524817-\$ or US-620018-\$ or US-5098861-\$ or US-4825018-\$ or US-598861-\$ or US-4825018-\$ or US-598861-\$ or US-2020008463-\$ or US-20200096717-\$ or US-20200084663-\$ or US-20200096717-\$ or US-20200086470-\$ or US-2020009798-\$ or US-20200086465-\$ or US-2020009798-\$ or US-20200072200-\$ or US-2020006649-\$ or US-20200072200-\$ or US-2020006849-\$ or US-20200012677-\$ or US-2020012677-\$ or US-202010277-\$ or US-202010277-\$ or US-202010277-\$ or US-202010277-\$ or US-202010277-\$ or US-202010277-\$ or US-2020002329-\$).did.) and SOI and ('tungsten or 'W) and silicide semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 2 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 2 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 3 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and (('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 semiconductor and ('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 6 semiconductor and ('tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.7") - 7 Semiconductor and ('tungsten or W) same (silane or "S					
US-5470411-\$ or US-536361-\$ or US-543394-\$ or US-546631-\$ or US-543394-\$ or US-5436943-\$ or US-5334394-\$ or US-5395481-\$ or US-5395481-\$ or US-5395481-\$ or US-5395481-\$ or US-5395481-\$ or US-5391257-\$ or US-5395481-\$ or US-5391257-\$ or US-5391257-\$ or US-5391257-\$ or US-5391257-\$ or US-5391267-\$ or US-5314678-\$ or US-5314678-\$ or US-5314678-\$ or US-5308776-\$ or US-528322-\$ or US-529305-\$ or US-528322-\$ or US-529305-\$ or US-528322-\$ or US-529305-\$ or US-4829018-\$ or US-4826787-\$ or US-4829018-\$ or US-4826787-\$ or US-4829018-\$ or US-4826787-\$ or US-200200137265-\$ or US-20020094663-\$ or US-20020094663-\$ or US-2002009617-\$ or US-20020094663-\$ or US-200200964670-\$ or US-200200964670-\$ or US-200200986469-\$ or US-20020092344-\$ or US-20020022337-\$ or US-20010002239-\$), did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46					
US-5492859-\$ or US-5466631-\$ or US-545399231-\$ or US-5459843-\$ or US-5399231-\$ or US-5399281-\$ or US-5399231-\$ or US-5397555-\$ or US-5397555-\$ or US-5374581-\$ or US-5374581-\$ or US-5374581-\$ or US-5374329-\$ or US-5374581-\$ or US-536824-\$ or US-5326776-\$ or US-536824-\$ or US-5328776-\$ or US-5268776-\$ or US-52747748-\$ or US-5250460-\$ or US-5277748-\$ or US-5250460-\$ or US-5229305-\$ or US-482678-\$ or US-5168078-\$ or US-5269861-\$ or US-482678-\$ or US-482678-\$ or US-482678-\$ or US-2002009617-\$ or US-20020094663-\$ or US-200200974663-\$ or US-20020006419-\$ or US-200200022337-\$ or US-200200022337-\$ or US-20020022337-\$ or US-200200022337-\$ or US-20020022337-\$ or US-20010012677-\$ or US-20010002379-\$, oid. and SOI and (tungsten or W) ame (silane or "SiH.sub.4") same (silane or "SiH.su				ľ	
US-5453394-S or US-5395481-S or US-5391257-\$ or US-5395481-S or US-5391257-\$ or US-5395481-S or US-5374581-\$ or US-5374329-\$ or US-5374581-\$ or US-5374329-\$ or US-5374581-\$ or US-5374329-\$ or US-5324678-\$ or US-5310446-\$ or US-530876-\$ or US-5277748-\$ or US-530876-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5258322-\$ or US-529305-\$ or US-46829018-\$ or US-5229305-\$ or US-4829018-\$ or US-5229305-\$ or US-4752590-\$), did. or (US-2002016603-\$ or US-20020037265-\$ or US-20020096717-\$ or US-2002008463-\$ or US-20020096717-\$ or US-20020084645-\$ or US-20020096719-\$ or US-20020084645-\$ or US-20020006419-\$ or US-20020084844-\$ or US-200200062419-\$ or US-20020084844-\$ or US-20020022344-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20010002329-\$), did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 2 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 3 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 2 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 3 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 4 semiconductor and ((WSiN) same silane same ammonia) - 5 semiconductor and ((WSiN) same silane same ammonia)					
US-5399231-\$ or US-5395581-\$ or US-539755-\$ or US-53971581-\$ or US-538755-\$ or US-5374581-\$ or US-536725-\$ or US-5374581-\$ or US-5366924-\$ or US-5374581-\$ or US-5366924-\$ or US-5324678-\$ or US-5366924-\$ or US-5324678-\$ or US-536924-\$ or US-536976-\$ or US-5259460-\$ or US-5277748-\$ or US-5259460-\$ or US-5279305-\$ or US-5259460-\$ or US-5289305-\$ or US-482678-\$ or US-5289305-\$ or US-48269018-\$ or US-4826787-\$ or US-20020094663-\$ or US-20020094663-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086465-\$ or US-20020090798-\$ or US-20020086465-\$ or US-20020090798-\$ or US-20020086465-\$ or US-200200072201-\$ or US-20020008445-\$ or US-20020008445-\$ or US-20020002337-\$ or US-20020008445-\$ or US-20020002337-\$ or US-2002002344-\$ or US-2001002329-\$, idid.) and SOI and (tungsten or W) asme silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3") - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (si					
US-5391257-\$ or US-5387555-\$ or US-5391297-\$ or US-5371037-\$ or US-5371037-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310466-\$ or US-5258322-\$ or US-5210467-\$ or US-5258322-\$ or US-5224617-\$ or US-528322-\$ or US-5224617-\$ or US-528322-\$ or US-5229305-\$ or US-5168078-\$ or US-5229305-\$ or US-4020918-\$ or US-4020918-\$ or US-4020918-\$ or US-4020918-\$ or US-4020918-\$ or US-4020918-\$ or US-20020094617-\$ or US-20020094663-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020096717-\$ or US-200200946465-\$ or US-20020072201-\$ or US-20020002334-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-2001001239-\$).did.) and Soll and (tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46	1				
US-5374581-\$ or US-5374329-\$ or US-5374581-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5324678-\$ or US-5210446-\$ or US-5208776-\$ or US-5229305-\$ or US-5250460-\$ or US-529305-\$ or US-5168078-\$ or US-529305-\$ or US-4029018-\$ or US-529305-\$ or US-4029018-\$ or US-529305-\$ or US-40200137265-\$ or US-200200160603-\$ or US-20020094663-\$ or US-20020090778-\$ or US-20020094665-\$ or US-20020096717-\$ or US-20020094665-\$ or US-20020006849-\$ or US-200200072200-\$ or US-20020006849-\$ or US-20020004864-\$ or US-20020002314-\$ or US-20020002337-\$ or US-2002002344-\$ or US-20010012677-\$ or US-20010002329-\$) did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UN same demunonia or "NH.sub.3")) - 46 Semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 Semiconductor and ((tungsten or W) same silicide same UN same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten or W) same silicide same UN same (ammonia or "NH.sub.3")) - 2 Semiconductor and ((tungsten or W) same silicide same UN same (ammonia or "NH.sub.3")) - 3 Semiconductor and ((tungsten or W) same silicide same UN same (ammonia or "NH.sub.3")) - 4 Semiconductor and ((tungsten or W) same silicide same UN same (ammonia or "NH.sub.3")) - 5 Semiconductor and ((tungsten or W) same silicide or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 6 Semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 7 Semiconductor and ((WSiN) same silane same and ammonia - 8 Semiconductor and ((WSiN) same silane same and ammonia - 9 Semiconductor and ((WSiN) same silane same and ammonia					
US-5371037-\$ or US-5366924-\$ or US-5308776-\$ or US-5301046-\$ or US-5308776-\$ or US-527748-\$ or US-528322-\$ or US-524817-\$ or US-5258322-\$ or US-524817-\$ or US-5258322-\$ or US-524817-\$ or US-5258322-\$ or US-5229305-\$ or US-5168078-\$ or US-5229305-\$ or US-4829018-\$ or US-4826787-\$ or US-4929018-\$ or US-4920096717-\$ or US-2002004663-\$ or US-20020096717-\$ or US-20020086470-\$ or US-20020096717-\$ or US-20020086470-\$ or US-2002008649-\$ or US-20020086470-\$ or US-20020068419-\$ or US-20020022337-\$ or US-2002002234-\$ or US-200100122677-\$ or US-200100122677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W) same silicide same (WI same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (Silane or "SiH.sub.4") same (silane or "NH.sub.3")) - 5 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NN.sub.3")) - 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NN.sub.3")) - 2 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NN.sub.3")) - 2 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NN.sub.3")) - 2 semiconductor and ((tungsten with silicide) or (wSi or WSiN)).ti. and silane and ammonia - 2 semiconductor and ((tungsten with silicide) or (wSi or WSiN)).ti. and silane and ammonia - 2 semiconductor and ((WSiN) same silane same ammonia) - 3 semiconductor and ((WSiN) same silane same ammonia) - 4 semiconductor and ((WSiN) same silane same ammonia) - 5 semiconductor and ((WSiN) same silane same ammonia)					
US-5324678-\$ or US-5310446-\$ or US-5258778-\$ or US-5258322-\$ or US-5244817-\$ or US-5258322-\$ or US-5244817-\$ or US-5258460-\$ or US-5259460-\$ or US-529305-\$ or US-5168078-\$ or US-529305-\$ or US-4752590-\$) did. or (US-20020160603-\$ or US-20220137265-\$ or US-20220996717-\$ or US-2022094663-\$ or US-2022094663-\$ or US-20220946645-\$ or US-20220064649-\$ or US-20220046465-\$ or US-2022006645-\$ or US-20220046465-\$ or US-20220072201-\$ or US-20200072201-\$ or US-202000202337-\$ or US-20200202337-\$ or US-2020022337-\$ or US-2020022337-\$ or US-20010012677-\$ or US-2010012677-\$ or US-20100212677-\$ or US-2010022077-\$ or US-20				1	
US-5308776-\$ or US-5277748-\$ or US-5259322-\$ or US-5259460-\$ or US-5259305-\$ or US-5260460-\$ or US-5229305-\$ or US-5168078-\$ or US-4825918-\$ or US-4826787-\$ or US-4829018-\$ or US-4826787-\$ or US-4829018-\$ or US-4826787-\$ or US-2002003137265-\$ or US-20020096717-\$ or US-20020086465-\$ or US-20020096798-\$ or US-20020086465-\$ or US-200200072201-\$ or US-20020086465-\$ or US-200200072201-\$ or US-20020022034-\$ or US-20020022034-\$ or US-2002002234-\$ or US-20020022337-\$ or US-20010021540-\$ or US-2001002329-\$).did.) and SOI and (tungsten or W) and silicide same UHV same deporption same silicide same UHV same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (silane same USPAT; silicide) or (wisi or wisin)).ti. and silane same use (silane or "SiH.sub.4") same (silane same use (sil]				
US-5259322-\$ or US-5244817-\$ or US-5250460-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-529305-\$ or US-5168078-\$ or US-529305-\$ or US-4752590-\$) did. or (US-20020160603-\$ or US-2020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020094663-\$ or US-20020094665-\$ or US-20020086469-\$ or US-20020072201-\$ or US-20020072200-\$ or US-2002002337-\$ or US-2002002334-\$ or US-2002002337-\$ or US-2002002334-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-2001001239-\$) did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (silm TDB (Silane or "SiH.sub.4") same (silane or "SiH.s				ĺ	
US-5250460-\$ or US-5229305-\$ or US-186078-\$ or US-186078-\$ or US-186078-\$ or US-4829018-\$ or US-4829018-\$ or US-4829018-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-200200966717-\$ or US-20020096663-\$ or US-20020096717-\$ or US-20020096663-\$ or US-20020096665-\$ or US-20020090738-\$ or US-20020086465-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020048844-\$ or US-2002002344-\$ or US-20020022337-\$ or US-2002002344-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-2001002239-\$).did.) and SOI and (tungsten or W) same silicide same UHV same deporption same (silcide same UHV same (ammonia or "NH.sub.3")) - 46 Semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 Semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silcide same UHV same (silcide same UHV same (silcide same UHV same (silcide same UHV same (silcide US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; U					1
US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4829018-\$ or US-4829018-\$ or US-4829018-\$ or US-4829018-\$ or US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020096465-\$ or US-20020086469-\$ or US-20020072200-\$ or US-20020072200-\$ or US-20020072200-\$ or US-20020002334-\$ or US-20020022344-\$ or US-2002002237-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-20010012677-\$ or US-2010012677-\$ o					
US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-200200137265-\$ or US-20020096717-\$ or US-200200086463-\$ or US-20020096717-\$ or US-20020086465-\$ or US-2002009678-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020048844-\$ or US-2002002344-\$ or US-20020022337-\$ or US-2002002344-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 5 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same					
US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-2002096717-\$ or US-2002009463-\$ or US-2002009798-\$ or US-20020086463-\$ or US-20020086469-\$ or US-20020086465-\$ or US-2002008201-\$ or US-20020072201-\$ or US-20020072200-\$ or US-2002008419-\$ or US-20020072307-\$ or US-2002002337-\$ or US-20010021540-\$ or US-2001002239-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; IBM_TDB					
US-20020137265-\$ or US-20020096717-\$ or US-2002009663-\$ or US-20020096645-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020084844-\$ or US-20020088445-\$ or US-20020086449-\$ or US-20020082337-\$ or US-20020086459-\$ or US-20020022337-\$ or US-20010021540-\$ or US-2001002677-\$ or US-2001002677-\$ or US-2001002677-\$ or US-2001002239-\$).did.) and SOI and (tungsten or W) ame silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46					
US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086455-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020072201-\$ or US-2002002337-\$ or US-20010021540-\$ or US-2001002677-\$ or US-20010020329-\$).did.) and SOI and (tungsten or W) ame silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (silane or "SiH.sub.4") same (silcide same (silane or "SiH.sub.4") same (ammonia or USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPACBUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPAT; USPAT; USPAT; USPACBUB; EPO; JPO; DERWENT; IBM TDB USP					l .
US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20010012677-\$ or US-20010012677-\$ or US-2001002329-\$).did.) and SOI and (tungsten or W) and silicide same UHV same deporption same (silane or "SiH.sub.4") same (silicide same UHV same deporption same (silicide same (silane or "SiH.sub.4") same (silicide same (silane or "SiH.sub.4") same (silicide same (silane or "SiH.sub.4") same (silicide same UHV same desorption same (silane or "NH.sub.3")) - 1 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (silane or "SiH.sub.4					
US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020022337-\$ or US-20020022344-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten or W) same (ammonia or "SiH.sub.4") same (silane or "SiH.sub.4") same (ammonia or EPC) JPO; DERWENT; IBM TDB (Silane or "SiH.sub.4") same (ammonia or EPC) JPO; DERWENT; IBM TDB (Silane or "SiH.sub.4") same (ammonia or EPC) JPO; DERWENT; IBM TDB (Silane or "SiH.sub.4") same silane same and ammonia - 2 semiconductor and ((WSiN) same silane same ammonia)					
US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-2002002344-\$ or US-20010012677-\$ or US-2001002329-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten or W) same (ammonia or "NH.sub.3")) - 2 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (silane or "					
US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 2 semiconductor and ((WSiN) same silane same ammonia) - 2 semiconductor and ((WSiN) same silane same ammonia) - 3 semiconductor and ((WSiN) same silane same ammonia)					1
US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (silane or "SiH.sub.4") same (silicide same (silane or "SiH.sub.4") same (silicide same (silane or "SiH.sub.4") same (silicide same UNPAT; US-PGPUB; EPO; JPO; DERWENT; IEM TDB USPAT; US-PGPUB; (silane or "SiH.sub.4") same (silane or USPAT; US-PGPUB; (silane or "SiH.sub.4") same (ammonia or USPAT; US-PGPUB; EPO; JPO; DERWENT; IEM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IE					1
US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 46 semiconductor and ((tungsten or W) same (ammonia or "NH.sub.3")) 5 semiconductor and ((tungsten or W) same (ammonia or "NH.sub.3")) 6 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (silane or "SiH.sub.4") same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 7 1 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 8 conductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia 9 2 semiconductor and ((WSiN) same silane same ammonia) 1 2 semiconductor and ((WSiN) same silane same ammonia) 1 3 semiconductor and ((WSiN) same silane same ammonia) 2 4 conductor same (WSiN) same silane same ammonia) 2 5 semiconductor and ((WSiN) same silane same ammonia)					
US-20010002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and (tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 5 semiconductor and ((tungsten or W) same (ammonia or "NH.sub.3")) 6 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 7 1 semiconductor and ((tungsten or W) same silicide same UHV same (ammonia or "NH.sub.3")) 8 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia 9 2 semiconductor and ((WSiN) same silane same ammonia) 1 semiconductor and ((WSiN) same silane same ammonia) 1 semiconductor and ((WSiN) same silane same ammonia)					
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(silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 46 semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 1 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia 2 semiconductor and ((WSiN) same silane same ammonia) 2 semiconductor and ((WSiN) same silane same ammonia) 3 semiconductor and ((WSiN) same silane same ammonia) 4 EPO; JPO; DERWENT; IBM TDB 2002/11/26 1		Ĭ			
semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 1 semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) 2 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia 2 semiconductor and ((WSiN) same silane same ammonia) 2 semiconductor and ((WSiN) same silane same ammonia) 3 semiconductor and ((WSiN) same silane same ammonia) 4 semiconductor and ((WSiN) same silane same ammonia)					
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silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten or W) same silane or "SiH.sub.4") same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten or W) same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia or (US-PGPUB; EPO; JPO; DERWENT; IBM TDB (US-PGPUB; EPO; JPO; DERWENT; IBM				IBM TDB	
(ammonia or "NH.sub.3")) Commonia or "NH.sub.3") EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	-	46	semiconductor and ((tungsten or W) same	USPAT;	2002/11/26 15:32
- 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 2 semiconductor and ((WSiN) same silane same ammonia) - 2 semiconductor and ((WSiN) same silane same ammonia) - 3 semiconductor and ((WSiN) same silane same ammonia) - 4 color transfer or W) same silane same silane same ammonia DERWENT; IBM TDB 2002/11/26 1			silicide same (silane or "SiH.sub.4") same	US-PGPUB;	
semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia semiconductor and ((WSiN) same silane same ammonia)			(ammonia or "NH.sub.3"))		
- 1 semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) - 1 semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia - 2 semiconductor and ((WSiN) same silane same ammonia) - 2 semiconductor and ((WSiN) same silane same ammonia) - 2 semiconductor and ((WSiN) same silane same ammonia)					
silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia semiconductor and ((WSiN) same silane same ammonia)					
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"NH.sub.3")) semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia semiconductor and ((WSiN) same silane same ammonia) semiconductor and ((WSiN) same silane same ammonia) semiconductor and ((WSiN) same silane same ammonia) 2 co02/11/26 1 US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	1				
semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia 2 semiconductor and ((WSiN) same silane same ammonia) 1 IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	1				
semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia semiconductor and ((WSiN) same silane same ammonia) semiconductor and ((WSiN) same silane same ammonia) semiconductor and ((WSiN) same silane same ammonia) 2 0002/11/26 1 2002/11/26 1 2002/11/26 1 2002/11/26 1			"NH.sub.3"))		
silicide) or (WSi or WSiN)).ti. and silane and ammonia Semiconductor and ((WSiN) same silane same ammonia) Semiconductor and ((WSiN) same silane same ammonia) Semiconductor and ((WSiN) same silane same ammonia) Semiconductor and ((WSiN) same silane same uspāt; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					0000/11/05 15 :-
and ammonia and ammonia EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT; IBM_TDB	-	1			2002/11/26 15:42
- 2 semiconductor and ((WSiN) same silane same USPĀT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB					
semiconductor and ((WSiN) same silane same USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			and ammonia		
semiconductor and ((WSiN) same silane same USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
ammonia) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		_	iducken and (/MGiN) same silens same		2002/11/26 15:45
EPO; JPO; DERWENT; IBM_TDB	-	2			2002/11/20 13:43
DERWENT; IBM_TDB			anunonia)		
IBM_TDB]				
	1_	2519	semiconductor and (nitrid\$6 same tungsten		2002/11/26 15:48
adj silicide) US-PGPUB;		2310			
EPO; JPO;					
DERWENT;	1				
IBM TDB					

_	411	(semiconductor and (nitrid\$6 same tungsten	USPAT;	2002/11/26 15:56
		adj silicide)) and silane	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1
-	146	((semiconductor and (nitrid\$6 same	USPAT;	2002/11/26 15:52
		tungsten adj silicide)) and silane) and	US-PGPUB;	
		ammonia	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	semiconductor and (monolayer with	USPAT;	2002/11/26 15:56
		(tungsten adj silicide))	US-PGPUB;	
		(touring tour day of the country of	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	(semiconductor and (monolayer with	USPAT:	2002/11/26 15:56
		(tungsten adj silicide))) and silane	US-PGPUB;	
	}	(tungsten adj silicide/// and silane	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	1	((semiconductor and (nitrid\$6 same	USPĀT:	2002/11/26 16:31
-	1	tungsten adj silicide)) and silane) and	US-PGPUB;	2002/11/20 10:01
		nitrad\$6	EPO; JPO;	
		HILLIAGO	DERWENT;	
			IBM TDB	
	92		USPAT;	2002/11/26 16:32
-	92		US-PGPUB;	2002/11/20 10.32
		electrolessly)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
			USPAT;	2002/11/26 16:35
-	54			2002/11/26 16:33
		electrolessly)	US-PGPUB;	
			EPO; JPO;	1
	1		DERWENT;	
	_		IBM_TDB	2002/11/26 16:35
-	0		USPAT;	2002/11/26 16:35
		electrolessly with equivalent)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

70	(US-6362078-\$ or US-6057212-\$ or US-6423091-\$ or US-6455398-\$ or US-6429094-\$ or US-6427094-\$ or US-6417075-\$ or US-6410436-\$ or US-633202-\$ or US-6313012-\$ or US-6333202-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6150031-\$ or US-6121112-\$ or US-6163598-\$ or US-6121112-\$ or US-6103598-\$ or US-6121112-\$ or US-6103598-\$ or US-6054363-\$ or US-5965626-\$ or US-5985739-\$ or US-5966620-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-536361-\$ or US-5453944-\$ or US-549843-\$ or US-545394-\$ or US-549843-\$ or US-545395481-\$ or US-5399231-\$ or US-5397555-\$ or US-5397555-\$ or US-5397555-\$ or US-5399231-\$ or US-5397555-\$ or US-5399231-\$ or US-5397555-\$ or US-5395257-\$ or US-5397555-\$ or	USPAT; US-PGPUB	2002/11/26 14:41
17	US-5208776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-52580460-\$ or US-529305-\$ or US-5168078-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-2002009463-\$ or US-20020096717-\$ or US-20020096470-\$ or US-20020096470-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020048644-\$ or US-2002008649-\$ or US-20020048844-\$ or US-2002002344-\$ or US-20020048844-\$ or US-2002002344-\$ or US-20020048844-\$ or US-2002002344-\$ or US-2002002337-\$ or US-2001002234-\$ or US-2002002337-\$ or US-2001002234-\$ or US-20020022337-\$ or US-2001002239-\$).did. ((US-6362078-\$ or US-6057212-\$ or US-6429095-\$ or US-6429094-\$ or US-6429095-\$ or US-6429094-\$ or US-6429095-\$ or US-6429094-\$ or US-6306729-\$ or US-6410436-\$ or US-6306729-\$ or US-6410436-\$ or US-6150031-\$ or US-6150031-\$ or US-6150031-\$ or US-6150031-\$ or US-6150031-\$ or US-6150031-\$ or US-6150039-\$ or US-6150039-\$ or US-6150039-\$ or US-6150039-\$ or US-6150039-\$ or US-65054363-\$ or US-610165-\$ or US-5985739-\$ or US-5985739-\$ or US-5985739-\$ or US-59856620-\$ or US-5985739-\$ or US-5985029-\$ or US-5985739-\$ or US-5533394-\$ or US-5433843-\$ or US-5374581-\$ or US-5374329-\$ or US-5386094-\$ or US-5399231-\$ or US-539861-\$ or US-528322-\$ or US-539861-\$ or US-528322-\$ or US-5387555-\$ or US-5374581-\$ or US-536924-\$ or US-5308776-\$ or US-5387555-\$ or US-5374581-\$ or US-5208661-\$ or US-52090096717-\$ or US-52002004663-\$ or US-5209009798-\$ or US-520020034663-\$ or US-520020096798-\$ or US-520020034663-\$ or US-20020096798-\$ or US-20020094663-\$ or US-20020096717-\$ or US-20020004844-\$ or US-20020002334-\$ or US-20020002334-\$ or US	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:06

L Number	Hits	Search Text	DB	Time stamp
-	0	(semiconductor and (back with gate) and	USPAT;	2002/11/26 13:35
		(tungsten or W) and adhesive and SOI) and	US-PGPUB;	
		LTO	EPO; JPO;	1
1			DERWENT;	
			IBM_TDB	
- 1	42		USPAT;	2002/11/26 13:42
l i		(tungsten or W) and adhesive and SOI	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
- 1	453	semiconductor and SOI and (tungsten or W)	USPAT;	2002/11/26 13:52
1		and multilayer	US-PGPUB;	1
			EPO; JPO;	i
			DERWENT;	1
1			IBM_TDB	1
-	41	(semiconductor and SOI and (tungsten or W)	USPAT;	2002/11/26 13:54
		and multilayer) and adhesive	US-PGPUB;	
1			EPO; JPO;	İ
			DERWENT;	
1			IBM_TDB	
-	36	((semiconductor and SOI and (tungsten or	USPAT;	2002/11/26 13:58
i 1		W) and multilayer) and adhesive) not	US-PGPUB;	
İ		(semiconductor and (back with gate) and	EPO; JPO;	
		(tungsten or W) and adhesive and SOI)	DERWENT;	
			IBM TDB	
-	2992	((438/622) or (438/582-583) or (438/195)	USPĀT;	2002/11/26 14:09
		or (438/266) or (438/311) or (438/455) or	US-PGPUB	ł
		(438/591) or (438/682-683)).CCLS.		
- 1	213		USPAT;	2002/11/26 14:18
İ		or (438/266) or (438/311) or (438/455) or	US-PGPUB;	
		(438/591) or (438/682-683)).CCLS.) and	EPO; JPO;	
-		(back with gate)	DERWENT;	
		· ·	IBM TDB	
-	1345	((438/455) or (438/406) or (438/459) or	USPĀT;	2002/11/26 14:28
I		(438/479)).CCLS.	US-PGPUB	
-	525	(((438/455) or (438/406) or (438/459) or	USPAT;	2002/11/26 14:29
I		(438/479)).CCLS.) and (tungsten or W)	US-PGPUB;	
			EPO; JPO;	
I			DERWENT;	
I			IBM TDB	

-	56	((US-6362078-\$ or US-6057212-\$ or	USPAT;	2002/11/26 15:23
	l	US-4335391-\$ or US-6455398-\$ or	US-PGPUB;	
	1	US-6429095-\$ or US-6429094-\$ or	EPO; JPO;	
		US-6417075-\$ or US-6410436-\$ or	DERWENT;	
	1	US-6333202-\$ or US-6313012-\$ or	IBM TDB	
	1	US-6306729-\$ or US-6221738-\$ or	_	
	1	US-6150031-\$ or US-6146979-\$ or	ł	
		US-6143628-\$ or US-6121112-\$ or	1	į.
		US-6103598-\$ or US-6103009-\$ or		
		US-6100165-\$ or US-6054363-\$ or		
		US-6045626-\$ or US-5985739-\$ or		
		US-5966620-\$ or US-5937312-\$ or		
		US-5856229-\$ or US-5773355-\$).did. or	1	
1	1	(US-5670411-\$ or US-5536361-\$ or		
		US-5492859-\$ or US-5466631-\$ or		
İ	,	US-5453394-\$ or US-5439843-\$ or		
	1	US-5399231-\$ or US-5395481-\$ or	İ	
		US-5391257-\$ or US-5387555-\$ or		
		US-5374581-\$ or US-5374329-\$ or		
ì	l	US-5371037-\$ or US-5366924-\$ or		
}	1	US-5324678-\$ or US-5310446-\$ or		
		US-5308776-\$ or US-5277748-\$ or		
		US-5258322-\$ or US-5244817-\$ or		
		US-5250460-\$ or US-5229305-\$ or		
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